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FDC608PZ

P-Channel 2.5V Specified PowerTrench® MOSFET

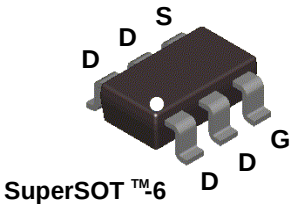
General Description

This P-Channel 2.5V specified MOSFET is produced using ON Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

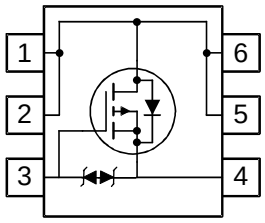
These devices are well suited for battery power applications: load switching and power management, battery power circuits, and DC/DC conversions.

Features

- –5.8 A, –20 V. $R_{DS(ON)}$ = 30 mΩ @ V_{GS} = –4.5 V
  $R_{DS(ON)}$ = 43 mΩ @ V_{GS} = –2.5 V
- Low Gate Charge
- High performance trench technology for extremely low $R_{DS(ON)}$
- SuperSOT ™ –6 package: small footprint (72% smaller than standard SO–8) low profile (1mm thick).



SuperSOT ™-6



Absolute Maximum Ratings

T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		–20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Drain Current – Continuous	(Note 1a)	–5.8	A
	– Pulsed		–20	
P_D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.608Z	FDC608PZ	7''	8mm	3000 units

October-2017, Rev. 2

Publication Order Number:
FDC608PZ/D

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = –250 μA	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = –250 μA,Referenced to 25°C		–10		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = –16 V, V_{GS} = 0 V			–1	μA
I_{GSS}	Gate–Body Leakage	V_{GS} = ±12 V, V_{DS} = 0 V			±10	μA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = –250 μA	–0.4	–1.0	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = –250 μA,Referenced to 25°C		3		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = –4.5V, I_D = –5.8 A V_{GS} = –2.5V, I_D = –5.0 A V_{GS} = –4.5V,I_D = –5.8A,T_J=125°C		26 38 35	30 43	mΩ
$I_{D(on)}$	On–State Drain Current	V_{GS} = –4.5 V, V_{DS} = –5 V	–20			A
g_{FS}	Forward Transconductance	V_{DS} = –10 V, I_D = –5.8 A		22		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = –10 V, V_{GS} = 0 V, f = 1.0 MHz		1330		pF
C_{oss}	Output Capacitance			270		pF
C_{rss}	Reverse Transfer Capacitance			230		pF
R_G	Gate Resistance	V_{GS} = 15 mV, f = 1.0 MHz		12		Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = –10 V, I_D = –1 A, V_{GS} = –4.5 V, R_{GEN} = 6 Ω		13	24	ns
t_r	Turn–On Rise Time			8	16	ns
$t_{d(off)}$	Turn–Off Delay Time			91	145	ns
t_f	Turn–Off Fall Time			60	96	ns
Q_g	Total Gate Charge	V_{DS} = –10 V, I_D = –5.8 A, V_{GS} = –4.5 V		17	23	nC
Q_{gs}	Gate–Source Charge			3		nC
Q_{gd}	Gate–Drain Charge			6		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				–1.3	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = –1.3 A (Note 2)		–0.7	–1.2	V
t_{rr}	Diode Reverse Recovery Time	I_F = –5.8 A, d_{iF}/d_t = 100A/μs		40	60	ns
Q_{rr}	Diode Reverse Recovery Charge	I_F = –5.8 A, d_{iF}/d_t = 100A/μs		15	23	nC

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a. 78°C/W when mounted on a 1in^2 pad of 2oz copper on FR-4 board.

b. 156°C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Typical Characteristics

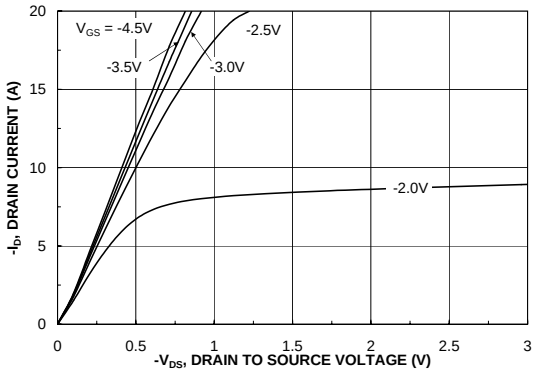


Figure 1. On-Region Characteristics.

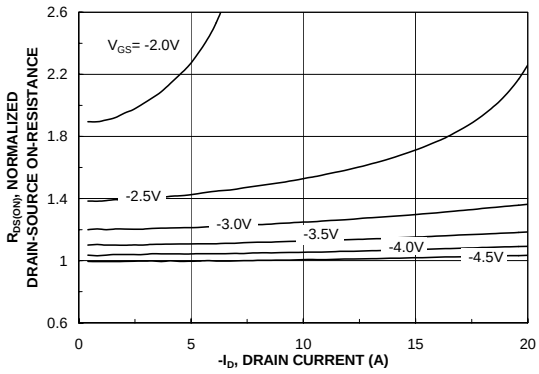


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

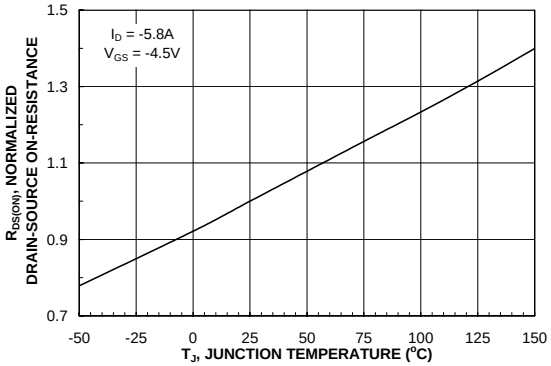


Figure 3. On-Resistance Variation with Temperature.

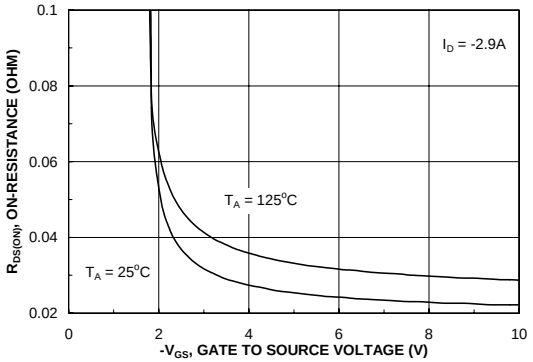


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

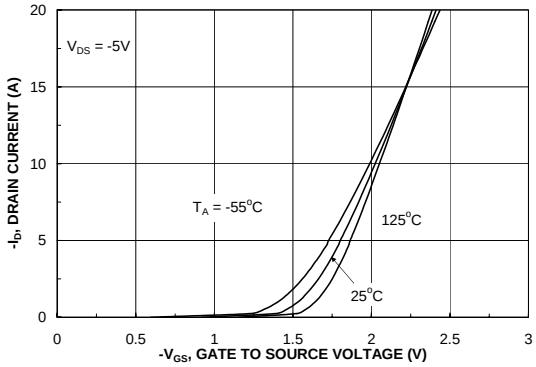


Figure 5. Transfer Characteristics.

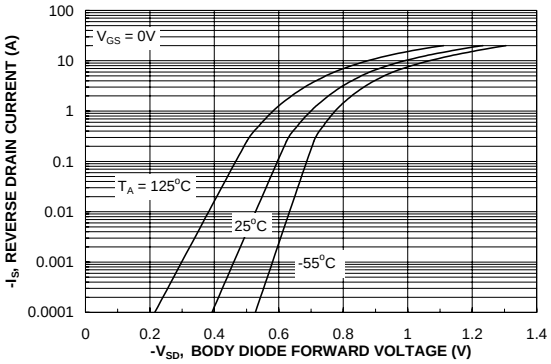


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

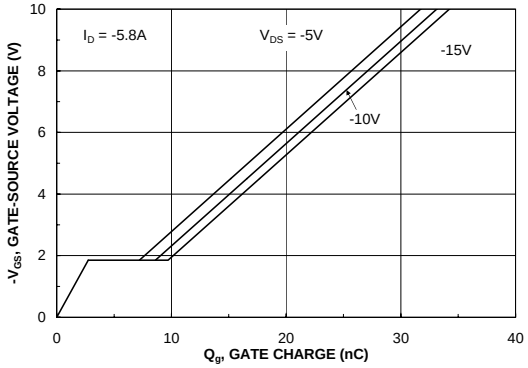


Figure 7. Gate Charge Characteristics.

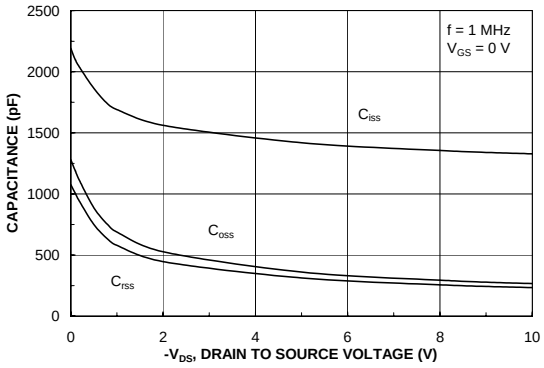


Figure 8. Capacitance Characteristics.

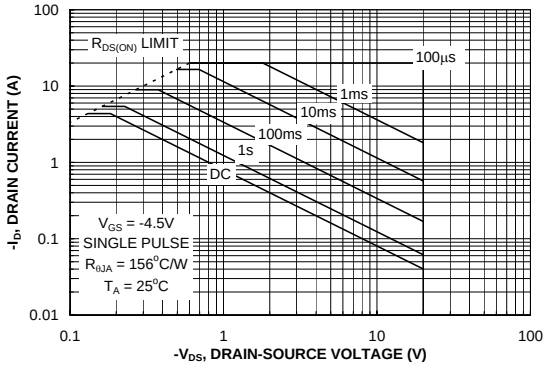


Figure 9. Maximum Safe Operating Area.

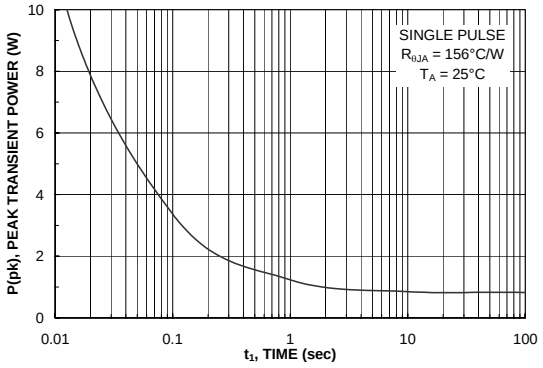


Figure 10. Single Pulse Maximum Power Dissipation.

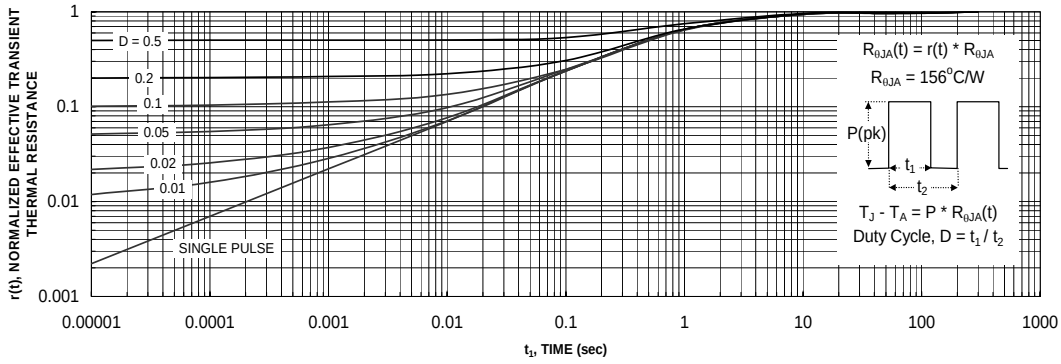


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

PUBLICATION ORDERING INFORMATION

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